Johann P Reithmaier

List of Publications by Year
in descending order

474 papers	11,676 citations	61857 43 h-index	40881 93 g-index
478 all docs	478 docs citations	478 times ranked	7333 citing authors

#	Article	IF	Citations
1	On the principle operation of tunneling injection quantum dot lasers. Progress in Quantum Electronics, 2022, 81, 100362.	3.5	7
2	High optical gain in InP-based quantum-dot material monolithically grown on silicon emitting at telecom wavelengths. Semiconductor Science and Technology, 2022, 37, 055005.	1.0	2
3	1.5-Âµm Indium Phosphide-based Quantum Dot Lasers and Optical Amplifiers. , 2022, , .		1
4	Optical and Spin Properties of NV Center Ensembles in Diamond Nano-Pillars. Nanomaterials, 2022, 12, 1516.	1.9	5
5	Steering coherence in quantum dots by carriers injection via tunneling. Nanophotonics, 2022, .	2.9	0
6	Magneto-Optical Characterization of Trions in Symmetric InP-Based Quantum Dots for Quantum Communication Applications. Materials, 2021, 14, 942.	1.3	9
7	Azido-Functionalized Aromatic Phosphonate Esters in ^RPOSS-Cage-Supported Lanthanide Ion (Ln = La, Nd, Dy, Er) Coordination. Inorganic Chemistry, 2021, 60, 5297-5309.	1.9	9
8	1.5-μm Indium Phosphide-Based Quantum Dot Lasers and Optical Amplifiers: The Impact of Atom-Like Optical Gain Material for Optoelectronics Devices. IEEE Nanotechnology Magazine, 2021, 15, 23-36.	0.9	9
9	InP-based single-photon sources operating at telecom C-band with increased extraction efficiency. Applied Physics Letters, 2021, 118, .	1.5	21
10	Quantum-Dot Based Vertical External-Cavity Surface-Emitting Lasers With High Efficiency. IEEE Photonics Technology Letters, 2021, 33, 719-722.	1.3	1
11	Room-temperature coherent revival in an ensemble of quantum dots. Physical Review Research, 2021, 3, .	1.3	5
12	Spin memory effect in charged single telecom quantum dots. Optics Express, 2021, 29, 34024.	1.7	3
13	Influence of surface termination of ultrananocrystalline diamond films coated on titanium on response of human osteoblast cells: A proteome study. Materials Science and Engineering C, 2021, 128, 112289.	3.8	5
14	Optical Quality of InAs/InP Quantum Dots on Distributed Bragg Reflector Emitting at 3rd Telecom Window Grown by Molecular Beam Epitaxy. Materials, 2021, 14, 6270.	1.3	4
15	Spin memory effect in charged single telecom quantum dots: erratum. Optics Express, 2021, 29, 36460.	1.7	0
16	Quantum coherent revival in a room-temperature quantum-dot optical amplifier: a route towards practical quantum information processing. , 2021, , .		0
17	Highâ€Purity Triggered Singleâ€Photon Emission from Symmetric Single InAs/InP Quantum Dots around the Telecom Câ€Band Window. Advanced Quantum Technologies, 2020, 3, 1900082.	1.8	35
18	Functionalised phosphonate ester supported lanthanide (Ln = La, Nd, Dy, Er) complexes. Dalton Transactions, 2020, 49, 16683-16692.	1.6	12

#	ARTICLE	IF	CITATIONS
19	Telecom wavelength InP-based L3 photonic crystal cavities: Properties of the cavity ground mode. AIP Conference Proceedings, 2020, , .	0.3	2
20	Coherence Time Prolongation in a Room Temperature Quantum Dot Ensemble. , 2020, , .		0
21	Fabrication and Characterization of Single-Crystal Diamond Membranes for Quantum Photonics with Tunable Microcavities. Micromachines, 2020, 11, 1080.	1.4	8
22	Optical and Electronic Properties of Symmetric <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>In</mml:mi><mml:mi>As</mml:mi></mml:mrow><mml:mo>/</mml:mo><mml:mo stretchy="false">(</mml:mo><mml:mrow><mml:mrow><mml:mi>In</mml:mi><mml:mo>,</mml:mo><mml:mspace Tj ETQq0 0 0 rgBT	1.5	10
23	Mode properties of telecom wavelength InP-based high-(Q/V) L4/3 photonic crystal cavities. Nanotechnology, 2020, 31, 315703.	1.3	9
24	Resonant and Nonresonant Tunneling Injection Processes in Quantum Dot Optical Gain Media. ACS Photonics, 2020, 7, 602-606.	3.2	2
25	Novel Ultra Localized and Dense Nitrogen Delta-Doping in Diamond for Advanced Quantum Sensing. Nano Letters, 2020, 20, 3192-3198.	4.5	16
26	Temperature resistant fast In_xGa_{1âˆ’x}As / GaAs quantum dot saturable absorber for the epitaxial integration into semiconductor surface emitting lasers. Optics Express, 2020, 28, 20954.	1.7	6
27	Fabrication of Diamond AFM Tips for Quantum Sensing. NATO Science for Peace and Security Series B: Physics and Biophysics, 2020, , 171-185.	0.2	1
28	Co-Occurrence of Resonance and Non-Resonance Tunneling Injection Processes in Quantum Dot Gain Media. , 2020, , .		0
29	Development of a Planarization Process for the Fabrication of Nanocrystalline Diamond Based Photonic Structures. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900314.	0.8	3
30	Fabrication of Nanopillars on Nanocrystalline Diamond Membranes for the Incorporation of Color Centers. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900233.	0.8	4
31	Comparison between InP-based quantum dot lasers with and without tunnel injection quantum well and the impact of rapid thermal annealing. Journal of Crystal Growth, 2019, 516, 34-39.	0.7	6
32	Optimization of size uniformity and dot density of InxGa1âˆ’xAs/GaAs quantum dots for laser applications in 1â€‰Âµm wavelength range. Journal of Crystal Growth, 2019, 517, 1-6.	0.7	6
33	Antimicrobial propensity of ultrananocrystalline diamond films with embedded silver nanodroplets. Diamond and Related Materials, 2019, 93, 168-178.	1.8	10
34	Quantum Nano-Jewelry: Plasmonic Addressing of Single-Photon Emitters in High-Quality Diamond Nanostructures. , 2019, , .		0
35	Excited states of neutral and charged excitons in single strongly asymmetric InP-based nanostructures emitting in the telecom C band. Physical Review B, 2019, 100, .	1.1	9
36	Coherent light matter interactions in nanostructure based active semiconductor waveguides operating at room temperature. Applied Physics Reviews, 2019, 6, 041317.	5.5	3

#	Article	IF	Citations
37	Deterministic Arrays of Epitaxially Grown Diamond Nanopyramid<i>s</i> with Embedded Siliconâ€Vacancy Centers. Advanced Optical Materials, 2019, 7, 1800715.	3.6	20
38	Comparison of quantum dot lasers with and without tunnel-injection quantum well. , 2019, , .		2
39	Narrow Linewidth InAs/InP Quantum Dot DFB Laser. , 2019, , .		2
40	Fabrication of highly dense arrays of nanocrystalline diamond nanopillars with integrated silicon-vacancy color centers during the growth. Optical Materials Express, 2019, 9, 4545.	1.6	8
41	Large linewidth reduction in semiconductor lasers based on atom-like gain material. Optica, 2019, 6, 1071.	4.8	41
42	MOICANA: monolithic cointegration of QD-based InP on SiN as a versatile platform for the demonstration of high-performance and low-cost PIC transmitters. , 2019, , .		3
43	Photonic engineering of highly linearly polarized quantum dot emission at telecommunication wavelengths. Physical Review B, 2018, 97, .	1.1	12
44	Telecom wavelength single quantum dots with very small excitonic fine-structure splitting. Applied Physics Letters, 2018, 112, .	1.5	40
45	Growth and optical characteristics of InAs quantum dot structures with tunnel injection quantum wells for 1.55â€¯<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.gif" overflow="scroll"><mml:mrow><mml:mi mathvariant="normal">Î¼</mml:mi></mml:mrow></mml:math>m high-speed lasers. Journal of Crystal Growth, 2018, 491, 20-25.	0.7	9
46	Control of Dynamic Properties of InAs/InAlGaAs/InP Hybrid Quantum Wellâ€Quantum Dot Structures Designed as Active Parts of 1.55â€‰Î¼m Emitting Lasers. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700455.	0.8	8
47	Spectral Characteristics of Narrow Linewidth InAs/InP Quantum Dot Distributed Feedback Lasers. , 2018, , .		1
48	1.5 Î¼m Quantum Dot Lasers and Amplifiers. , 2018, , .		0
49	IIIâ€"V on Silicon Nanocomposites. Semiconductors and Semimetals, 2018, , 27-42.	0.4	2
50	Electron and hole spin relaxation in InP-based self-assembled quantum dots emitting at telecom wavelengths. Physical Review B, 2018, 98, .	1.1	3
51	Nanostructured modified ultrananocrystalline diamond surfaces as immobilization support for lipases. Diamond and Related Materials, 2018, 90, 32-39.	1.8	3
52	Telecom Wavelength Nanophotonic Elements for Quantum Communication. , 2018, , .		0
53	Carrier dynamics in a tunneling injection quantum dot semiconductor optical amplifier. Physical Review B, 2018, 98, .	1.1	12
54	Quantum Information Technology and Sensing Based on Color Centers in Diamond. NATO Science for Peace and Security Series B: Physics and Biophysics, 2018, , 193-214.	0.2	0

#	Article	IF	Citations
55	Carrier relaxation bottleneck in type-II InAs/InGaAlAs/InP(001) coupled quantum dots-quantum well structure emitting at 1.55 Î¼m. Applied Physics Letters, 2018, 112, 221901.	1.5	8
56	Ramsey fringes in a room-temperature quantum-dot semiconductor optical amplifier. Physical Review B, 2018, 97, .	1.1	7
57	Temperature stability of static and dynamic properties of 155 Âµm quantum dot lasers. Optics Express, 2018, 26, 6056.	1.7	47
58	Strongly temperature-dependent recombination kinetics of a negatively charged exciton in asymmetric quantum dots at 1.55â€‰Âµm. Applied Physics Letters, 2018, 113, 043103.	1.5	6
59	Carrier transfer efficiency and its influence on emission properties of telecom wavelength InP-based quantum dot â€“ quantum well structures. Scientific Reports, 2018, 8, 12317.	1.6	6
60	Homoepitaxial Diamond Structures with Incorporated SiV Centers. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800371.	0.8	9
61	On the relationship between electrical and electro-optical characteristics of InAs/InP quantum dot lasers. Journal of Applied Physics, 2018, 124, .	1.1	4
62	High Performance 1550 nm Quantum Dot Semiconductor Optical Amplifiers Operating at 25-100 Â°C. , 2018, , .		3
63	Telecom wavelength emitting single quantum dots coupled to InP-based photonic crystal microcavities. Applied Physics Letters, 2017, 110, .	1.5	26
64	High-bandwidth temperature-stable 1.55-Î¼m quantum dot lasers. Proceedings of SPIE, 2017, , .	0.8	4
65	Carrier delocalization in InAs/InGaAlAs/InP quantum-dash-based tunnel injection system for 1.55 Âµm emission. AIP Advances, 2017, 7, 015117.	0.6	10
66	Ultra-fast charge carrier dynamics across the spectrum of an optical gain media based on InAs/AlGaInAs/InP quantum dots. AIP Advances, 2017, 7, 035122.	0.6	10
67	Widely tunable narrow-linewidth 1.5 <i>Î¼</i>m light source based on a monolithically integrated quantum dot laser array. Applied Physics Letters, 2017, 110, .	1.5	26
68	Patterning of the surface termination of ultrananocrystalline diamond films for guided cell attachment and growth. Surface and Coatings Technology, 2017, 321, 229-235.	2.2	22
69	Lateral carrier diffusion in InGaAs/GaAs coupled quantum dot-quantum well system. Applied Physics Letters, 2017, 110, .	1.5	7
70	Exciton lifetime and emission polarization dispersion in strongly in-plane asymmetric nanostructures. Physical Review B, 2017, 96, .	1.1	28
71	Interplay of morphology, composition, and optical properties of InP-based quantum dots emitting at the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>1.55</mml:mn><mml:mspace width="0.28em" /><mml:mi>Î¼</mml:mi><mml:mi mathvariant="normal">m</mml:mi></mml:mrow></mml:math> telecom wavelength. Physical Review B, 2017, 96, .	1.1	15
72	Confinement regime in self-assembled InAs/InAlGaAs/InP quantum dashes determined from exciton and biexciton recombination kinetics. Applied Physics Letters, 2017, 111, 253106.	1.5	10

#	ARTICLE	IF	CITATIONS
73	Introduction to the Special Issue on Semiconductor Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-3.	1.9	539
74	Static and dynamic characteristics of an InAs/InP quantum-dot optical amplifier operating at high temperatures. Optics Express, 2017, 25, 27262.	1.7	16
75	Acceleration of the nonlinear dynamics in p-doped indium phosphide nanoscale resonators. Optics Letters, 2017, 42, 795.	1.7	6
76	The issue of 0D-like ground state isolation in GaAs- and InP-based coupled quantum dots-quantum well systems. Journal of Physics: Conference Series, 2017, 906, 012019.	0.3	1
77	InAs on InP Quantum Dashes as Single Photon Emitters at the Second Telecommunication Window: Optical, Kinetic, and Excitonic Properties. Acta Physica Polonica A, 2017, 132, 382-386.	0.2	2
78	InP-Based Quantum Dot Lasers. , 2017, , .		0
79	Coherent control in room-temperature quantum dot semiconductor optical amplifiers using shaped pulses. Optica, 2016, 3, 570.	4.8	7
80	Tailoring the photoluminescence polarization anisotropy of a single InAs quantum dash by a post-growth modification of its dielectric environment. Journal of Applied Physics, 2016, 120, .	1.1	8
81	Coherent control in InAs / InP quantum dot optical amplifiers operating at room-temperature. , 2016, , .		0
82	Exciton spin relaxation in InAs/InGaAlAs/InP(001) quantum dashes emitting near 1.55Î¼m. Applied Physics Letters, 2016, 109, 193108.	1.5	9
83	Single-photon emission of InAs/InP quantum dashes at 1.55â€‰<i>Î¼</i>m and temperatures up to 80â€‰K. Applied Physics Letters, 2016, 108, .	1.5	38
84	Strong attachment of circadian pacemaker neurons on modified ultrananocrystalline diamond surfaces. Materials Science and Engineering C, 2016, 64, 278-285.	3.8	11
85	Functionalization of nanocrystalline diamond films with phthalocyanines. Applied Surface Science, 2016, 379, 415-423.	3.1	3
86	Plasma surface fluorination of ultrananocrystalline diamond films. Surface and Coatings Technology, 2016, 302, 448-453.	2.2	12
87	III-V integration on Si for photonics. , 2016, , .		3
88	1.5 Âµm quantum dot lasers for data and telecom applications. , 2016, , .		3
89	Large anisotropy of electron and hole<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>factors in infrared-emitting InAs/InAlGaAs self-assembled quantum dots. Physical Review B, 2016, 93, .	1.1	27
90	Temperature-Insensitive High-Speed Directly Modulated 1.55-<inline-formula> <tex-math notation="LaTeX">$mu ext{m}$ </tex-math> </inline-formula> Quantum Dot Lasers. IEEE Photonics Technology Letters, 2016, 28, 2451-2454.	1.3	32

#	Article	IF	Citations
91	Excitonic fine structure and binding energies of excitonic complexes in single InAs quantum dashes. Physical Review B, 2016, 94, .	1.1	18
92	(Invited) III-V / Si Integration for Photonics. ECS Transactions, 2016, 72, 171-179.	0.3	6
93	High-speed directly modulated 1.5 Î¼m quantum dot lasers. Proceedings of SPIE, 2016, , .	0.8	0
94	Coherent photocurrent spectroscopy of single InP-based quantum dots in the telecom band at 1.5ÂÂµm. Applied Physics B: Lasers and Optics, 2016, 122, 1.	1.1	4
95	Incorporation and study of SiV centers in diamond nanopillars. Diamond and Related Materials, 2016, 64, 64-69.	1.8	22
96	Probing the carrier transfer processes in a self-assembled system with In 0.3 Ga 0.7 As/GaAs quantum dots by photoluminescence excitation spectroscopy. Superlattices and Microstructures, 2016, 93, 214-220.	1.4	2
97	Narrow-linewidth 1.5Î¼m quantum dot distributed feedback lasers. Proceedings of SPIE, 2016, , .	0.8	4
98	High-speed directly modulated 1.5Î¼m quantum dot lasers. Proceedings of SPIE, 2016, , .	0.8	5
99	Effect of Dielectric Medium Anisotropy on the Polarization Degree of Emission from a Single Quantum Dash. Acta Physica Polonica A, 2016, 129, A-48-A-52.	0.2	2
100	1.5Î¼m quantum dot laser material with high temperature stability of threshold current density and external differential efficiency. , 2016, , .		6
101	Coherent Control by Shaped Pulses in Room Temperature InAs/InP Quantum Dot Optical Amplifiers. , 2016, , .		0
102	High-Speed InP-Based Quantum Dot Lasers With Low Temperature Sensitivity. , 2016, , .		0
103	Electron and hole<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>factors in InAs/InAlGaAs self-assembled quantum dots emitting at telecom wavelengths. Physical Review B, 2015, 92, .	1.1	23
104	Quantum Coherent Interactions in Room Temperature InAs/InP Quantum Dot Amplifiers. , 2015, , .		0
105	Site-controlled growth of GaAs nanoislands on pre-patterned silicon substrates. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 443-448.	0.8	5
106	Nonlinear pulse propagation in InAs/InP quantum dot optical amplifiers: Rabi oscillations in the presence of nonresonant nonlinearities. Physical Review B, 2015, 91, .	1.1	16
107	Breakthroughs in Photonics 2014: Time-Scale-Dependent Nonlinear Dynamics in InAs/InP Quantum Dot Gain Media: From High-Speed Modulation to Coherent Lightâ€“Matter Interactions. IEEE Photonics Journal, 2015, 7, 1-7.	1.0	0
108	Towards faster InP photonic crystal all-optical-gates. , 2015, , .		0

#	Article	IF	Citations
109	High-density 1.54 Î¼m InAs/InGaAlAs/InP(100) based quantum dots with reduced size inhomogeneity. Journal of Crystal Growth, 2015, 425, 299-302.	0.7	38
110	Interface structure and strain state of InAs nano-clusters embedded in silicon. Acta Materialia, 2015, 90, 133-139.	3.8	16
111	Magnetic field control of the neutral and charged exciton fine structure in single quantum dashes emitting at 1.55â€‰Î¼m. Applied Physics Letters, 2015, 106, 053114.	1.5	21
112	Controlled modification of the electronic wavefunction and direct observation of quantum decoherence in a room-temperature quantum-dot semiconductor optical amplifier. , 2014, , .		0
113	Phonon-assisted radiative recombination of excitons confined in strongly anisotropic nanostructures. Physical Review B, 2014, 90, .	1.1	22
114	Single photon emission at 1.55â€‰Î¼m from charged and neutral exciton confined in a single quantum dash. Applied Physics Letters, 2014, 105, 021909.	1.5	43
115	Cell adhesion and growth on ultrananocrystalline diamond and diamond-like carbon films after different surface modifications. Applied Surface Science, 2014, 297, 95-102.	3.1	46
116	Rabi oscillations in a room-temperature quantum dash semiconductor optical amplifier. Physical Review B, 2014, 90, .	1.1	25
117	Carrier dynamics in inhomogeneously broadened InAs/AlGaInAs/InP quantum-dot semiconductor optical amplifiers. Applied Physics Letters, 2014, 104, .	1.5	14
118	Coherent control in a semiconductor optical amplifier operating at room temperature. Nature Communications, 2014, 5, 5025.	5.8	20
119	High Speed 1.55 Î¼m InAs/InGaAlAs/InP Quantum Dot Lasers. IEEE Photonics Technology Letters, 2014, 26, 11-13.	1.3	33
120	Low-density InP-based quantum dots emitting around the 1.5â€‰<i>Î¼</i>m telecom wavelength range. Applied Physics Letters, 2014, 104, .	1.5	23
121	Nanostructured hybrid material based on highly mismatched <scp>III</scp>â€“<scp>V</scp> nanocrystals fully embedded in silicon. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 817-822.	0.8	10
122	Static and dynamic characteristics of InAs/AlGaInAs/InP quantum dot lasers operating at 1550 nm. , 2013, , .		1
123	New class of 1.55 μm quantum dot lasers for future high data rate optical communication. , 2013, , .		0
124	Bright light emissions with narrow spectral linewidths from single InAs/GaAs quantum dots directly grown on silicon substrates. Applied Physics Letters, 2013, 102, .	1.5	6
125	Electronic structure, morphology and emission polarization of enhanced symmetry InAs quantum-dot-like structures grown on InP substrates by molecular beam epitaxy. Journal of Applied Physics, 2013, 114, .	1.1	28
126	Investigation of <scp>NV</scp> centers in nanoâ€•and ultrananocrystalline diamond pillars. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 2066-2073.	0.8	11

#	Article	IF	Citations
127	Telecom-wavelength (1.5â€‰<i>Î¼</i>m) single-photon emission from InP-based quantum dots. Applied Physics Letters, 2013, 103, .	1.5	111
128	Grafting of manganese phthalocyanine on nanocrystalline diamond films. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 2048-2054.	0.8	12
129	Wavelength conversion at 10 GHz using a two-color photonic crystal gate. , 2013, , .		0
130	Heterodyne pump probe measurements of nonlinear dynamics in an indium phosphide photonic crystal cavity. Applied Physics Letters, 2013, 103, .	1.5	29
131	Highly non-linear phenomena and coherent effects in 1500 nm QD lasers and amplifiers. , 2013, , .		0
132	Nonlinear pulse propagation in a quantum dot laser. Optics Express, 2013, 21, 5715.	1.7	7
133	High modal gain 1.5 Î¼m InP based quantum dot lasers: dependence of static properties on the active layer design. , 2013, , .		0
134	Reactive ion etching of nanocrystalline diamond for the fabrication of one-dimensional nanopillars. Diamond and Related Materials, 2013, 36, 58-63.	1.8	13
135	High-gain wavelength-stabilized 1.55 <i>Î¼</i>m InAs/InP(100) based lasers with reduced number of quantum dot active layers. Applied Physics Letters, 2013, 102, .	1.5	27
136	Investigation of NV centers in diamond nanocrystallites and nanopillars. Physica Status Solidi (B): Basic Research, 2013, 250, 48-50.	0.7	3
137	Rabi oscillations and self-induced transparency in InAs/InP quantum dot semiconductor optical amplifier operating at room temperature. Optics Express, 2013, 21, 26786.	1.7	33
138	InP-based 1.5 µm quantum dot lasers: Static and dynamic properties. , 2013, , .		1
139	Exciton and biexciton dynamics in single self-assembled InAs/InGaAlAs/InP quantum dash emitting near 1.55â€‰<i>Î¼</i>m. Applied Physics Letters, 2013, 103, .	1.5	33
140	All-optical signal processing at 10â€‰GHz using a photonic crystal molecule. Applied Physics Letters, 2013, 103, .	1.5	24
141	Direct growth of IIIâ€“V quantum dots on silicon substrates: structural and optical properties. Semiconductor Science and Technology, 2013, 28, 094004.	1.0	13
142	Two-color switching and wavelength conversion at 10 GHz using a Photonic Crystal molecule. , 2013, , .		1
143	Gas chopping etching process for InP based nanostructures with high aspect ratios. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 060601.	0.6	0
144	Extreme nonlinearities in InAs/InP nanowire gain media: the two-photon induced laser. Optics Express, 2012, 20, 5987.	1.7	9

#	Article	IF	Citations
145	Complex characterization of short-pulse propagation through InAs/InP quantum-dash optical amplifiers: from the quasi-linear to the two-photon-dominated regime. Optics Express, 2012, 20, 347.	1.7	8
146	Influence of electronic coupling on the radiative lifetime in the (In,Ga)As/GaAs quantum dotâ€“quantum well system. Physical Review B, 2012, 85, .	1.1	25
147	On the mechanisms of energy transfer between quantum well and quantum dashes. Journal of Applied Physics, 2012, 112, 033520.	1.1	6
148	Growth-Temperature Dependence of Wetting Layer Formation in High Density InGaAs/GaAs Quantum Dot Structures Grown by Droplet Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 085501.	0.8	4
149	Temperature effects on the characterization of new quantum dot dual mode lasers for terahertz generation. Proceedings of SPIE, 2012, , .	0.8	1
150	Tribological properties of nanocrystalline diamond films deposited by hot filament chemical vapor deposition. AIP Advances, 2012, 2, .	0.6	19
151	Thermally tunable DFB dual mode laser diode by an external platinum thin-film heater for THz generation. , 2012, , .		0
152	Preâ€patterned silicon substrates for the growth of IIIâ€“V nanostructures. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 2402-2410.	0.8	12
153	Recent advances in high-speed lasers and amplifiers based on 1.5 µm QD/QDash material. , 2012, , .		0
154	Influence of the surface termination of ultrananocrystalline diamond/amorphous carbon composite films on their interaction with neurons. Diamond and Related Materials, 2012, 26, 60-65.	1.8	16
155	Nanostructuring of silicon substrates for the site-controlled growth of GaAs/In0.15Ga0.85As/GaAs nanostructures. Microelectronic Engineering, 2012, 97, 59-63.	1.1	4
156	15-W Fiber-Coupled Quantum-Dot Pump Module. IEEE Photonics Technology Letters, 2012, 24, 1030-1032.	1.3	0
157	Digital modulation at 20 GBit/s of an InAs/InGaAlAs/InP quantum dot laser operating in the telecom wavelength range. , 2012, , .		1
158	High-Speed Low-Noise InAs/InAlGaAs/InP 1.55-$mu{m m}$ Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2012, 24, 809-811.	1.3	30
159	Height-driven linear polarization of the surface emission from quantum dashes. Semiconductor Science and Technology, 2012, 27, 105022.	1.0	17
160	Low temperature growth of nanocrystalline and ultrananocrystalline diamond films: A comparison. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1664-1674.	0.8	24
161	Single-photon emission from single InGaAs/GaAs quantum dots grown by droplet epitaxy at high substrate temperature. Nanoscale Research Letters, 2012, 7, 493.	3.1	11
162	Relation between small and large signal modulation capabilities in highly nonlinear quantum dot lasers for optical telecommunication. , 2012, , .		0

#	Article	IF	Citations
163	Stability of the surface termination of differently modified ultrananocrystalline diamond/amorphous carbon composite films. Surface and Coatings Technology, 2012, 209, 184-189.	2.2	10
164	Growth-Temperature Dependence of Wetting Layer Formation in High Density InGaAs/GaAs Quantum Dot Structures Grown by Droplet Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 085501.	0.8	2
165	1.55 Î¼m High-Speed Quantum Dot Lasers for Telecommunication Applications. , 2012, , .		0
166	InP Based Quantum Dot/Dash Material for High Speed Optoelectronic Devices: Recent Results and Prospects. , 2012, , .		0
167	High gain 1.55â€‚Î¼m diode lasers based on InAs quantum dot like active regions. Applied Physics Letters, 2011, 98, .	1.5	58
168	High-gain InP-based quantum dot lasers for telecommunication applications. , 2011, , .		0
169	Nanocrystalline diamond containing hydrogels and coatings for acceleration of osteogenesis. Diamond and Related Materials, 2011, 20, 165-169.	1.8	17
170	Plasma amination of ultrananocrystalline diamond/amorphous carbon composite films for the attachment of biomolecules. Diamond and Related Materials, 2011, 20, 254-258.	1.8	24
171	1.3-mum Two-Section DBR Lasers Based on Surface Defined Gratings for High-Speed Telecommunication. IEEE Photonics Technology Letters, 2011, 23, 411-413.	1.3	10
172	Carrier transfer in the GaAs-based tunnel injection quantum well-quantum dots structures. AIP Conference Proceedings, 2011, , .	0.3	0
173	Multi Wavelength Characterization of Ultra Fast Carrier Dynamics in InAs/InP Quantum Dash Optical Amplifiers. , 2011, , .		0
174	UNCD/a-C nanocomposite films for biotechnological applications. Surface and Coatings Technology, 2011, 206, 667-675.	2.2	13
175	Tribological properties of ultrananocrystalline diamond films in various test atmosphere. Tribology International, 2011, 44, 2042-2049.	3.0	38
176	Optical studies of (AsSe)100â^'x Sb x thin films. Applied Physics A: Materials Science and Processing, 2011, 104, 959-962.	1.1	2
177	On the development of the morphology of ultrananocrystalline diamond films. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 70-80.	0.8	20
178	Growth of InAs quantum dots and dashes on silicon substrates: Formation and characterization. Journal of Crystal Growth, 2011, 323, 422-425.	0.7	14
179	1100â€‰nm InGaAs/(Al)GaAs quantum dot lasers for high-power applications. Journal Physics D: Applied Physics, 2011, 44, 145104.	1.3	6
180	Ultrafast cross saturation dynamics in inhomogeneously broadened InAs/InP quantum dash optical amplifiers. Applied Physics Letters, 2011, 98, .	1.5	10

#	Article	IF	Citations
181	Temperature Dependence of Photoluminescence from Epitaxial InGaAs/GaAs Quantum Dots with High Lateral Aspect Ratio. Acta Physica Polonica A, 2011, 120, 883-887.	0.2	6
182	Slow light using cross gain modulation in a quantum dash semiconductor optical amplifier. , 2011, , .		0
183	Two Photon Induced Lasing in 1550 nm Quantum Dash Optical Gain Media. , 2011, , .		0
184	Tunnel injection structures based on InGaAs/GaAs quantum dots: optical properties and energy structure. Journal of Physics: Conference Series, 2010, 245, 012047.	0.3	0
185	High optical quality site-controlled quantum dots. Microelectronic Engineering, 2010, 87, 1357-1359.	1.1	1
186	Investigation of the UV/O₃ treatment of ultrananocrystalline diamond films. Surface and Interface Analysis, 2010, 42, 1152-1155.	0.8	18
187	Spontaneously Localized Photonic Modes Due to Disorder in the Dielectric Constant. , 2010, , .		0
188	A nearly instantaneous gain response in quantum dash based optical amplifiers. Applied Physics Letters, 2010, 97, .	1.5	23
189	Time-resolved photoluminescence spectroscopy of an InGaAs/GaAs quantum well-quantum dots tunnel injection structure. Applied Physics Letters, 2010, 96, .	1.5	14
190	Influence of the As2/As4 growth modes on the formation of quantum dot-like InAs islands grown on InAlGaAs/InP (100). Applied Physics Letters, 2010, 96, 191903.	1.5	48
191	Electrical properties of ultrananocrystalline diamond/amorphous carbon nanocomposite films. Diamond and Related Materials, 2010, 19, 449-452.	1.8	18
192	Ultrananocrystalline Diamond / Amorphous Carbon Composite Films â€" Deposition, Characterization and Applications. Solid State Phenomena, 2010, 159, 49-55.	0.3	0
193	Multi-wavelength femtosecond pump-probe characterization of 1550 nm InAs/InP quantum dash optical amplifiers. , 2010, , .		0
194	Site-controlled InAs quantum dots grown on a 55 nm thick GaAs buffer layer. Applied Physics Letters, 2009, 95, 243106.	1.5	15
195	Microthermography of diode lasers: The impact of light propagation on image formation. Journal of Applied Physics, 2009, 105, 014502.	1.1	16
196	Optically pumped lasing from a single pillar microcavity with InGaAs/GaAs quantum well potential fluctuation quantum dots. Journal of Applied Physics, 2009, 105, 053513.	1.1	4
197	Introduction to the Issue on Semiconductor Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 480-481.	1.9	0
198	Complex (As2S3)(100âˆ’)(AgI) chalcogenide glasses for gas sensors. Sensors and Actuators B: Chemical, 2009, 143, 395-399.	4.0	22

#	Article	IF	Citations
199	Electromodulation spectroscopy of In0.53Ga0.47As/In0.53Ga0.23Al0.24As quantum wells. Superlattices and Microstructures, 2009, 46, 425-434.	1.4	3
200	Wavelength stabilized quantum dot lasers for high power applications. Physica Status Solidi (B): Basic Research, 2009, 246, 872-875.	0.7	2
201	Structural and optical properties of ultrananocrystalline diamond / InGaAs/GaAs quantum dot structures. Thin Solid Films, 2009, 518, 1489-1492.	0.8	2
202	Control of dot geometry and photoluminescence linewidth of InGaAs/GaAs quantum dots by growth conditions. Journal of Crystal Growth, 2009, 311, 1783-1786.	0.7	6
203	Spectroscopic studies of (AsSe)100â^'xAgx thin films. Applied Surface Science, 2009, 255, 9691-9694.	3.1	7
204	Characterization of pulsed laser deposited chalcogenide thin layers. Applied Surface Science, 2009, 255, 5318-5321.	3.1	16
205	High-Power Tunnel-Injection 1060-nm InGaAsâ€"(Al)GaAs Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2009, 21, 999-1001.	1.3	25
206	Wettability and protein adsorption on ultrananocrystalline diamond/amorphous carbon composite films. Diamond and Related Materials, 2009, 18, 895-898.	1.8	29
207	Influence of the nucleation density on the structure and mechanical properties of ultrananocrystalline diamond films. Diamond and Related Materials, 2009, 18, 151-154.	1.8	15
208	Bulk temperature mapping of broad area quantum dot lasers: modeling and micro-thermographic analysis. Proceedings of SPIE, 2009, , .	0.8	1
209	Engineered quantum dot structures: fabrication and applications. Proceedings of SPIE, 2009, , .	0.8	0
210	Study of (As2Se3)100-X(AgI)X Thin Films Prepared by Pld and Vte Methods. NATO Science for Peace and Security Series B: Physics and Biophysics, 2009, , 329-334.	0.2	3
211	Nanostructured Semiconductor Materials For Optoelectronic Applications. NATO Science for Peace and Security Series B: Physics and Biophysics, 2009, , 447-476.	0.2	3
212	Tunneling-injection High-power 1060-nm Quantum Dot Laser with Improved Temperature Stability. , 2009, , .		0
213	2D substrate imaging of a tapered laser cavity based on InGaAs quantum dots. IOP Conference Series: Materials Science and Engineering, 2009, 6, 012010.	0.3	0
214	Microstructural, MOrphological And Optical Characterization of As2Se3â€"As2 Te3â€"Sb2Te3 Amorphous Layers. NATO Science for Peace and Security Series B: Physics and Biophysics, 2009, , 357-360.	0.2	0
215	Nanocrystalline diamond/amorphous carbon composite coatings for biomedical applications. Diamond and Related Materials, 2008, 17, 882-887.	1.8	18
216	Strong excitonâ€"photon coupling in semiconductor quantum dot systems. Semiconductor Science and Technology, 2008, 23, 123001.	1.0	59

#	Article	IF	Citations
217	Direct observation of the coherent spectral hole in the noise spectrum of a saturated InAs/InP quantum dash amplifier operating near 1550 nm. Optics Express, 2008, 16, 2141.	1.7	11
218	Cross talk free multi channel processing of 10 Gbit/s data via four wave mixing in a 1550 nm InAs/InP quantum dash amplifier. Optics Express, 2008, 16, 19072.	1.7	17
219	Transient electromagnetically induced transparency in self-assembled quantum dots. Applied Physics Letters, 2008, 92, .	1.5	93
220	Cross talk free multi channel processing of 10 Gbit/s data via four wave mixing in a 1550 nm InAs/InP quantum dash amplifier. , 2008, , .		0
221	GaInAs/(Al)GaAs quantum-dot lasers with high wavelength stability. Semiconductor Science and Technology, 2008, 23, 085022.	1.0	19
222	High power, low threshold 1060-nm InGaAs/AlGaAs quantum dot lasers. , 2008, , .		1
223	Singlemode InAs/InP quantum dash distributed feedback lasers emitting in 1.9â€…[micro sign]m range. Electronics Letters, 2008, 44, 527.	0.5	9
224	Semiconductor optical amplifiers with nanostructured gain material. , 2008, , .		4
225	Singlemode tapered quantum dot laser diodes with monolithically integrated feedback gratings. Electronics Letters, 2007, 43, 926.	0.5	6
226	Influence of geometric disorder on the band structure of a photonic crystal: Experiment and theory. Physical Review B, 2007, 75, .	1.1	13
227	Contactless electroreflectance of InAsâˆ•In0.53Ga0.23Al0.24As quantum dashes grown on InP substrate: Analysis of the wetting layer transition. Journal of Applied Physics, 2007, 101, 013507.	1.1	6
228	Theoretical and experimental investigations on temperature induced wavelength shift of tapered laser diodes based on InGaAsâˆ•GaAs quantum dots. Applied Physics Letters, 2007, 91, 051126.	1.5	11
229	Highly efficient and compact photonic wire splitters on GaAs. Applied Physics Letters, 2007, 91, 221102.	1.5	10
230	Efficient energy transfer in InAs quantum dash based tunnel-injection structures at low temperatures. , 2007, , .		4
231	InAs/InP Quantum-Dash Lasers and Amplifiers. Proceedings of the IEEE, 2007, 95, 1779-1790.	16.4	76
232	Bioproperties of nanocrystalline diamond/amorphous carbon composite films. Diamond and Related Materials, 2007, 16, 735-739.	1.8	45
233	DFB Lasers With Deeply Etched Vertical Grating Based on InAsâ€“InP Quantum-Dash Structures. IEEE Photonics Technology Letters, 2007, 19, 264-266.	1.3	8
234	Modal Analysis of Large Spot Size, Low Output Beam Divergence Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2007, 19, 916-918.	1.3	7

#	Article	IF	Citations
235	Some features of chalcohalide glassy Geâ€"Sâ€"AgI thin films. Journal of Physics and Chemistry of Solids, 2007, 68, 936-939.	1.9	3
236	Photoreflectance and contactless electroreflectance of an InAs quantum dash laser structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 350-352.	0.8	2
237	Band gap dependence of the recombination processes in InAs/GaAs quantum dots studied using hydrostatic pressure. Physica Status Solidi (B): Basic Research, 2007, 244, 82-86.	0.7	5
238	Thermal quenching of photoluminescence from InAsâˆ•In0.53Ga0.23Al0.24Asâˆ•InP quantum dashes with different sizes. Applied Physics Letters, 2006, 89, 151902.	1.5	23
239	Photoreflectance-probed excited states in InAsâˆ•InGaAlAs quantum dashes grown on InP substrate. Applied Physics Letters, 2006, 89, 031908.	1.5	40
240	Radiative emission dynamics of quantum dots in a single cavity micropillar. Physical Review B, 2006, 74, .	1.1	37
241	Ultrafast gain and index dynamics of quantum dash structures emitting at 1.55Î¼m. Applied Physics Letters, 2006, 89, 081102.	1.5	41
242	Optical properties of low-strained InxGa1âˆ'xAsâˆ•GaAs quantum dot structures at the two-dimensionalâ€"three-dimensional growth transition. Journal of Applied Physics, 2006, 100, 013503.	1.1	23
243	Coherent photonic coupling of semiconductor quantum dots. Optics Letters, 2006, 31, 1738.	1.7	43
244	Coherent photonic coupling of semiconductor quantum dots: erratum. Optics Letters, 2006, 31, 3507.	1.7	1
245	Influence of doping density on electron dynamics in GaAsâˆ•AlGaAs quantum cascade lasers. Journal of Applied Physics, 2006, 99, 103106.	1.1	47
246	Nanostructured semiconductors for optoelectronic applications. , 2006, , .		1
247	High power and very low noise operation at 1.3 and 1.5 Î¼m with quantum dot and quantum dash Fabry-Perot lasers for microwave links. , 2006, 6399, 158.		4
248	Influence of injector doping density and electron confinement on the properties of GaAs/Al0.45Ga0.55As quantum cascade lasers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 411-414.	0.8	4
249	Optical characteristics of lowly strained GaInAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3815-3818.	0.8	2
250	Scanning transmission electron microscopy of vertically stacked self organized quantum structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3947-3950.	0.8	2
251	Photoreflectance investigations of energy level structure of InAs quantum dashes embedded in InGaAs/InGaAlAs quantum well grown on InP substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3852-3855.	0.8	0
252	Strong and weak coupling of single quantum dot excitons in pillar microcavities. Physica Status Solidi (B): Basic Research, 2006, 243, 2224-2228.	0.7	7

#	Article	IF	Citations
253	Semiconductor quantum dots devices: Recent advances and application prospects. Physica Status Solidi (B): Basic Research, 2006, 243, 3981-3987.	0.7	15
254	Recent advances in nanophotonicsâ€"From physics to devices. Current Applied Physics, 2006, 6, e166-e171.	1.1	1
255	Structural and optical analysis of size-controlled InAs quantum dashes. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 108-110.	1.3	4
256	Magnetooptical investigations of single self assembled In0.3Ga0.7As quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 131-134.	1.3	4
257	Investigation of strong coupling between single quantum dot excitons and single photons in pillar microcavities. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 471-475.	1.3	7
258	Influence of the strain on the formation of GaInAs/GaAs quantum structures. Journal of Crystal Growth, 2006, 286, 6-10.	0.7	49
259	Strong coupling in a single quantum dot semiconductor microcavity system. , 2006, , .		2
260	Ultra-compact high transmittance photonic wire bends for monolithic integration on III/V-semiconductors. Electronics Letters, 2006, 42, 1280.	0.5	2
261	Mode switching and singlemode tuning in two-segment distributed feedback quantum cascade lasers. Electronics Letters, 2006, 42, 220.	0.5	4
262	Comparative Analysis of Î»â‰ˆ9Âµm GaAs/AlGaAs Quantum Cascade Lasers with Different Injector Doping. Materials Science Forum, 2006, 518, 29-34.	0.3	0
263	Photonic crystal quantum cascade lasers with improved threshold characteristics operating at room temperature. Applied Physics Letters, 2006, 89, 191113.	1.5	6
264	Photoreflectance determination of the wetting layer thickness in the InxGa1â^'xAsâ^•GaAs quantum dot system for a broad indium content range of 0.3â€"1. Journal of Applied Physics, 2006, 100, 103529.	1.1	21
265	Scanning transmission electron microscope study on vertically correlated InGaAsâ^•GaAs quantum dots. Applied Physics Letters, 2006, 89, 023121.	1.5	3
266	Self-gating in an electron Y-branch switch at room temperature. Applied Physics Letters, 2006, 89, 122109.	1.5	7
267	On the tunnel injection of excitons and free carriers from In0.53Ga0.47Asâ^•In0.53Ga0.23Al0.24As quantum well to InAsâ^•In0.53Ga0.23Al0.24As quantum dashes. Applied Physics Letters, 2006, 89, 061902.	1.5	17
268	Lasing in high-Q quantum-dot micropillar cavities. Applied Physics Letters, 2006, 89, 051107.	1.5	92
269	Photoreflectance investigation of InAs quantum dashes embedded in In0.53Ga0.47Asâ^•In0.53Ga0.23Al0.24As quantum well grown on InP substrate. Applied Physics Letters, 2006, 88, 141915.	1.5	13
270	Optical gain properties of InAsâ^•InAlGaAsâ^•InP quantum dash structures with a spectral gain bandwidth of more than 300nm. Applied Physics Letters, 2006, 89, 061107.	1.5	36

#	Article	IF	Citations
271	Widely tunable single-mode quantum cascade lasers with two monolithically coupled Fabry-PÃ©rot cavities. Applied Physics Letters, 2006, 89, 241126.	1.5	17
272	Dependence of saturation effects on electron confinement and injector doping in GaAsâˆ•Al0.45Ga0.55As quantum-cascade lasers. Applied Physics Letters, 2006, 88, 251109.	1.5	16
273	Very Low Noise and Reliable 1.55 Î¼m InP-Based Quantum-Dash Fabry-Perot Lasers for Microwave Links. , 2006, , .		0
274	System performance of a modern hollow-core optical fiber coupled to a quantum cascade laser: transmission efficiency and relative intensity noise. , 2005, , .		1
275	Gain and noise properties of InAs/InP quantum dash semiconductor optical amplifiers. , 2005, , .		0
276	Monomodige DFB-Quantenkaskadenlaser mit Metall-Bragg-RÃ¼ckkopplungsgittern (Single Mode) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	0.3	1
277	Reduction of the threshold current density of GaAs/AlGaAs quantum cascade lasers by optimized injector doping and growth conditions. Journal of Crystal Growth, 2005, 278, 775-779.	0.7	23
278	InP-based quantum dash lasers for wide gain bandwidth applications. Journal of Crystal Growth, 2005, 278, 346-350.	0.7	20
279	STEM-study of 1.3Î¼m InAs/InGaAs quantum dot structures. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 241-244.	1.3	3
280	Gain and noise saturation of wide-band InAs-InP quantum dash optical amplifiers: model and experiments. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1015-1026.	1.9	38
281	Device performance and wavelength tuning behavior of ultra-short quantum-cascade microlasers with deeply etched Bragg-mirrors. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1048-1054.	1.9	16
282	Cross-saturation dynamics in InAsâˆ•InP quantum dash optical amplifiers operating at 1550â€…nm. Electronics Letters, 2005, 41, 266.	0.5	6
283	GaAs-based four-channel photonic crystal quantum dot laser module operating at 1.3â€…[micro sign]m. Electronics Letters, 2005, 41, 1121.	0.5	0
284	High-power quantum dot lasers with improved temperature stability of emission wavelength for uncooled pump sources. Electronics Letters, 2005, 41, 1125.	0.5	30
285	Static and dynamic properties of laterally coupled DFB lasers based on InAsâˆ•InP QDash structures. Electronics Letters, 2005, 41, 808.	0.5	22
286	Structural Analysis of InAs Quantum Dashes Grown on InP Substrate by Scanning Transmission Electron Microscopy. AIP Conference Proceedings, 2005, , .	0.3	0
287	The Influence of Auger Processes on Recombination in Long-Wavelength InAs/GaAs Quantum Dots. AIP Conference Proceedings, 2005, , .	0.3	0
288	Integrated four-channel GaAs-based quantum dot laser module with photonic crystals. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 3193.	1.6	0

#	Article	IF	Citations
289	GaAs/AlGaAs-Quantenkaskaden-Laser (GaAs/AlGaAs Quantum Cascade Lasers). TM Technisches Messen, 2005, 72, .	0.3	1
290	Room temperature operation of ultra-short quantum cascade lasers with deeply etched Bragg mirrors. Electronics Letters, 2005, 41, 704.	0.5	4
291	Time-resolved chirp in an InAsâˆ•InP quantum-dash optical amplifier operating with 10Gbitâˆ•s data. Applied Physics Letters, 2005, 87, 021104.	1.5	19
292	Polarization-dependent optical properties of planar photonic crystals infiltrated with liquid crystals. Applied Physics Letters, 2005, 87, 121105.	1.5	23
293	Semiconductor quantum dot micropillar cavities for quantum electrodynamic experiments. , 2005, , .		1
294	Gain, index variation, and linewidth-enhancement factor in 980-nm quantum-well and quantum-dot lasers. IEEE Journal of Quantum Electronics, 2005, 41, 117-126.	1.0	24
295	Semiconductor quantum dot microcavity pillars with high-quality factors and enlarged dot dimensions. Applied Physics Letters, 2005, 86, 111105.	1.5	78
296	InP based lasers and optical amplifiers with wire-/dot-like active regions. Journal Physics D: Applied Physics, 2005, 38, 2088-2102.	1.3	134
297	Control of Vertically CoupledInGaAs/GaAsQuantum Dots with Electric Fields. Physical Review Letters, 2005, 94, 157401.	2.9	138
298	Optically probed wetting layer in InAs/InGaAlAs/InP quantum-dash structures. Applied Physics Letters, 2005, 86, 101904.	1.5	29
299	Size control of InAs quantum dashes. Applied Physics Letters, 2005, 86, 253112.	1.5	84
300	Quantum Dots: Building Blocks of Quantum Devices?. Advances in Solid State Physics, 2004, , 191-212.	0.8	0
301	Multiple wavelength amplification in wide band high power 1550â€...nm quantum dash optical amplifier. Electronics Letters, 2004, 40, 760.	0.5	40
302	GaAsâˆ•AlGaAs quantum cascade micro lasers based on monolithic semiconductor-air Bragg mirrors. Electronics Letters, 2004, 40, 120.	0.5	16
303	Photonic crystal waveguides with propagation losses in the 1â€,dBâˆ•mm range. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 3356.	1.6	8
304	Spectrally resolved dynamics of inhomogeneously broadened gain in InAsâˆ•InP1550nm quantum-dash lasers. Applied Physics Letters, 2004, 85, 5505-5507.	1.5	16
305	High brightness GaInAs/(Al)GaAs quantum-dot tapered lasers at 980 nm with high wavelength stability. Applied Physics Letters, 2004, 84, 2238-2240.	1.5	19
306	Strong coupling in a single quantum dotâ€"semiconductor microcavity system. Nature, 2004, 432, 197-200.	13.7	1,776

#	Article	IF	Citations
307	Carrier leakage suppression utilising short-period superlattices in 980 nm InGaAs/GaAs quantum well lasers. Physica Status Solidi (B): Basic Research, 2004, 241, 3405-3409.	0.7	1
308	Recombination mechanisms in InAs/InP quantum dash lasers studied using high hydrostatic pressure. Physica Status Solidi (B): Basic Research, 2004, 241, 3427-3431.	0.7	21
309	22-GHz Modulation Bandwidth of Long Cavity DBR Laser by Using a Weakly Laterally Coupled Grating Fabricated by Focused Ion Beam Lithography. IEEE Photonics Technology Letters, 2004, 16, 18-20.	1.3	23
310	High-Speed Coupled-Cavity Injection Grating Lasers With Tailored Modulation Transfer Functions. IEEE Photonics Technology Letters, 2004, 16, 1997-1999.	1.3	15
311	On the nature of quantum dash structures. Journal of Applied Physics, 2004, 95, 6103-6111.	1.1	87
312	High-brightness GaInAs/(Al)GaAs quantum dot tapered lasers at 980 nm with a high wavelength stability. , 2004, 5365, 60.		0
313	Lasers and amplifiers based on quantum-dot-like gain material. , 2004, , .		2
314	High-power and low-noise 1.55 Î¼m InP-based quantum dash lasers. , 2004, 5452, 22.		4
315	High-brightness (1 W with M2=2.9) GaInAs/(Al)GaAs index-guided quantum-dot tapered lasers at 980 nm with a high-wavelength stability. , 2004, 5452, 1.		1
316	Coherent InGaAsâˆ•GaAs laser arrays with laterally coupled distributed feedback gratings. Electronics Letters, 2004, 40, 118.	0.5	3
317	Measurements of gain and index dynamics in quantum dash semiconductor optical amplifiers. , 2004, , .		2
318	Multiple wavelength amplification in a high power InAs/InP quantum dash optical amplifier operating at 1.55 Âµm. , 2004, , .		0
319	The role of auger recombination in inas 1.3-Î¼m quantum-dot lasers investigated using high hydrostatic pressure. IEEE Journal of Selected Topics in Quantum Electronics, 2003, 9, 1300-1307.	1.9	57
320	Semiconductor quantum dots - A new class of gain materials for advanced optoelectronics. IEEE Circuits and Devices: the Magazine of Electronic and Photonic Systems, 2003, 19, 24-29.	0.8	7
321	Epitaxial growth of 1.55Î¼m emitting InAs quantum dashes on InP-based heterostructures by GS-MBE for long-wavelength laser applications. Journal of Crystal Growth, 2003, 251, 248-252.	0.7	64
322	Improved performance of MBE grown quantum-dot lasers with asymmetric dots in a well design emitting near 1.3Î¼m. Journal of Crystal Growth, 2003, 251, 742-747.	0.7	27
323	Photomodulation spectroscopy applied to low-dimensional semiconductor structures. Microelectronics Journal, 2003, 34, 351-353.	1.1	4
324	Decoherence and environment effects in single InGaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 7-10.	1.3	1

#	Article	IF	Citations
325	Recent advances in semiconductor quantum-dot lasers. Comptes Rendus Physique, 2003, 4, 611-619.	0.3	21
326	High-pressure studies of the recombination processes, threshold currents, and lasing wavelengths in InAs/GaInAs quantum dot lasers. Physica Status Solidi (B): Basic Research, 2003, 235, 407-411.	0.7	4
327	Spectral characteristics of single InAs/InGaAs quantum dots in a quantum well. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1133-1136.	0.8	0
328	Zeeman spectroscopy of single self-assembled InAs/InGaAlAs quantum dashes. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1161-1164.	0.8	1
329	Wavelength stabilized single-mode lasers by coupled micro-square resonators. IEEE Photonics Technology Letters, 2003, 15, 377-379.	1.3	11
330	Broad-band wavelength conversion based on cross-gain modulation and four-wave mixing in InAs-InP quantum-dash semiconductor optical amplifiers operating at 1550 nm. IEEE Photonics Technology Letters, 2003, 15, 563-565.	1.3	77
331	Magneto-optical investigations of single self-assembled InAs/InGaAlAs quantum dashes. Applied Physics Letters, 2003, 82, 2799-2801.	1.5	32
332	Tunable photonic crystals fabricated in III-V semiconductor slab waveguides using infiltrated liquid crystals. Applied Physics Letters, 2003, 82, 2767-2769.	1.5	128
333	Importance of Auger recombination in InAs 1.3â€…[micro sign]m quantum dot lasers. Electronics Letters, 2003, 39, 58.	0.5	24
334	High-power 980â€…nm quantum dot broad area lasers. Electronics Letters, 2003, 39, 1655.	0.5	28
335	Cross-gain modulation in inhomogeneously broadened gain spectra of InP-Based 1550 nm quantum dash optical amplifiers: Small-signal bandwidth dependence on wavelength detuning. Applied Physics Letters, 2003, 82, 4660-4662.	1.5	32
336	Enhanced direct-modulated bandwidth of 37â€…GHz by a multi-section laser with a coupled-cavity-injection-grating design. Electronics Letters, 2003, 39, 1592.	0.5	31
337	1.54â€…[micro sign]m singlemode InP-based Q-dash lasers. Electronics Letters, 2003, 39, 985.	0.5	15
338	Focused Ion Beam Technology for Optoelectronic Devices. AIP Conference Proceedings, 2003, , .	0.3	0
339	Correlation between the gain profile and the temperature-induced shift in wavelength of quantum-dot lasers. Applied Physics Letters, 2002, 81, 217-219.	1.5	86
340	Optical spectroscopy of single InAs/InGaAs quantum dots in a quantum well. Applied Physics Letters, 2002, 81, 4898-4900.	1.5	34
341	Near-field mapping of the electromagnetic field in confined photon geometries. Physical Review B, 2002, 66, .	1.1	19
342	High Performance 1.3 Âμm Quantum-Dot Lasers. Japanese Journal of Applied Physics, 2002, 41, 1158-1161.	0.8	20

#	Article	IF	Citations
343	Efficient light transmission through InP-based photonic crystal waveguides. Electronics Letters, 2002, 38, 178.	0.5	14
344	Long-wavelength InP-based quantum-dash lasers. IEEE Photonics Technology Letters, 2002, 14, 735-737.	1.3	166
345	Laterally coupled DBR laser emitting at 1.55 Î¼m fabricated by focused ion beam lithography. IEEE Photonics Technology Letters, 2002, 14, 1037-1039.	1.3	15
346	Wide range tunable laterally coupled distributed-feedback lasers based on InGaAs-GaAs quantum dots. IEEE Photonics Technology Letters, 2002, 14, 1246-1248.	1.3	25
347	InAsâˆ•InP 1550â€‰nm quantum dash semiconductor optical amplifiers. Electronics Letters, 2002, 38, 1350.	0.5	37
348	Fine structure of neutral and charged excitons in self-assembled In(Ga)As/(Al)GaAs quantum dots. Physical Review B, 2002, 65, .	1.1	933
349	Line narrowing in single semiconductor quantum dots: Toward the control of environment effects. Physical Review B, 2002, 66, .	1.1	78
350	Single-mode distributed feedback and microlasers based on quantum-dot gain material. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 1035-1044.	1.9	22
351	Deeply etched two-dimensional photonic crystals fabricated on GaAs/AlGaAs slab waveguides by using chemically assisted ion beam etching. Microelectronic Engineering, 2002, 61-62, 875-880.	1.1	22
352	Capture and confinement of light and carriers in graded-index quantum well laser structures. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 885-887.	1.3	1
353	GaAs based lasers for telecommunication. , 2002, , .		0
354	Semiconductor lasers with 2-D-photonic crystal mirrors based on a wet-oxidized Al2O3-mask. IEEE Photonics Technology Letters, 2001, 13, 406-408.	1.3	8
355	Edge-emitting microlasers with one active layer of quantum dots. IEEE Journal of Selected Topics in Quantum Electronics, 2001, 7, 300-305.	1.9	4
356	Complex coupled distributed-feedback and Bragg-reflector lasers for monolithic device integration based on focused-ion-beam technology. IEEE Journal of Selected Topics in Quantum Electronics, 2001, 7, 306-311.	1.9	13
357	Photon band gap systems from semiconductor microcavities. Synthetic Metals, 2001, 116, 457-460.	2.1	0
358	High-temperature operating 1.3-Î¼m quantum-dot lasers for telecommunication applications. IEEE Photonics Technology Letters, 2001, 13, 764-766.	1.3	59
359	Selective growth of InP on focused-ion-beam-modified GaAs surface by hydride vapor phase epitaxy. Applied Physics Letters, 2001, 79, 1885-1887.	1.5	13
360	High frequency characteristics of InAs/GaInAs quantum dot distributed feedback lasers emitting at 1.3 [micro sign]m. Electronics Letters, 2001, 37, 1223.	0.5	30

#	Article	IF	Citations
361	InAs/GaInAs quantum dot DFB lasers emitting at 1.3 [micro sign]m. Electronics Letters, 2001, 37, 634.	0.5	25
362	Photoreflectance spectroscopy of vertically coupled InGaAs/GaAs double quantum dots. Solid State Communications, 2001, 117, 401-406.	0.9	30
363	Lateral coupling â€" a material independent way to complex coupled DFB lasers. Optical Materials, 2001, 17, 19-25.	1.7	52
364	980 nm Quantum Dot Lasers with Very Small Threshold Current Densities. Physica Status Solidi (B): Basic Research, 2001, 224, 845-848.	0.7	0
365	Tertiarybutylarsine (TBAs) and -phosphine (TBP) as group V-precursors for gas source molecular beam epitaxy for optoelectronic applications. Journal of Crystal Growth, 2001, 227-228, 298-302.	0.7	1
366	Low threshold high efficiency MBE grown GaInAs/(Al)GaAs quantum dot lasers emitting at 980nm. Journal of Crystal Growth, 2001, 227-228, 1151-1154.	0.7	11
367	Nanoscale patterning by focused ion beam enhanced etching for optoelectronic device fabrication. Microelectronic Engineering, 2001, 57-58, 891-896.	1.1	6
368	Reactive ion etching of deeply etched DBR-structures with reduced air-gaps for highly reflective monolithically integrated laser mirrors. Microelectronic Engineering, 2001, 57-58, 593-598.	1.1	10
369	Two-dimensional photonic crystal laser mirrors. Semiconductor Science and Technology, 2001, 16, 227-232.	1.0	10
370	High-performance 980 nm quantum dot lasers for high-power applications. Electronics Letters, 2001, 37, 353.	0.5	40
371	12 [micro sign]m long edge-emitting quantum-dot laser. Electronics Letters, 2001, 37, 690.	0.5	17
372	Strain analysis and quantum well intermixing of a laterally modulated multiquantum well system produced by focused ion beam implantation. Journal Physics D: Applied Physics, 2001, 34, A11-A14.	1.3	0
373	Photonic defect states in chains of coupled microresonators. Physical Review B, 2001, 64, .	1.1	21
374	Quantum-dot microlasers. Electronics Letters, 2000, 36, 1548.	0.5	14
375	Bent laser cavity based on 2D photonic crystal waveguide. Electronics Letters, 2000, 36, 324.	0.5	13
376	Semiconductor photonic molecules. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 616-624.	1.3	11
377	Photon confinement effects â€" from physics to applications. Microelectronic Engineering, 2000, 53, 21-28.	1.1	6
378	GaSb/AlGaSb VCSEL structures and microcavities in the 1.5 Î¼m wavelength range. , 2000, , 627-639.		0

#	Article	IF	Citations
379	Polariton-polariton scattering in semiconductor microcavities: Experimental observation of thresholdlike density dependence. Physical Review B, 2000, 61, R2409-R2412.	1.1	51
380	Highly efficient GaInAs/(Al)GaAs quantum-dot lasers based on a single active layer versus 980 nm high-power quantum-well lasers. Applied Physics Letters, 2000, 77, 1419-1421.	1.5	92
381	Grazing-incidence diffraction strain analysis of a laterally-modulated multiquantum well system produced by focused-ion-beam implantation. Applied Physics Letters, 2000, 77, 4277-4279.	1.5	9
382	High-frequency properties of 1.55 Î¼m laterally complex coupled distributed feedback lasers fabricated by focused-ion-beam lithography. Applied Physics Letters, 2000, 77, 325-327.	1.5	20
383	Carrier and light trapping in graded quantum-well laser structures. Applied Physics Letters, 2000, 76, 3540-3542.	1.5	8
384	Highly Resolved Maskless Patterning on InP by Focused Ion Beam Enhanced Wet Chemical Etching. Japanese Journal of Applied Physics, 1999, 38, 6142-6144.	0.8	19
385	Short-cavity edge-emitting lasers with deeply etched distributed Bragg mirrors. Electronics Letters, 1999, 35, 154.	0.5	22
386	Strong variation of the excitongfactors in self-assembledIn0.60Ga0.40Asquantum dots. Physical Review B, 1999, 60, R8481-R8484.	1.1	37
387	High-performance GaInAs/GaAs quantum-dot lasers based on a single active layer. Applied Physics Letters, 1999, 74, 2915-2917.	1.5	86
388	1.55 Î¼m single mode lasers with complex coupled distributed feedback gratings fabricated by focused ion beam implantation. Applied Physics Letters, 1999, 75, 1491-1493.	1.5	19
389	Far-field emission pattern and photonic band structure in one-dimensional photonic crystals made from semiconductor microcavities. Physical Review B, 1999, 59, 10251-10254.	1.1	9
390	Magnetic-field dependence of the exciton-photon coupling in structured photonic cavities. Physical Review B, 1999, 60, 10695-10698.	1.1	6
391	Optical Demonstration of a Crystal Band Structure Formation. Physical Review Letters, 1999, 83, 5374-5377.	2.9	91
392	Improved carrier confinement in GaInAs/AlGaAs lasers by MBE grown short period superlattice quantum well barriers. Journal of Crystal Growth, 1999, 201-202, 914-918.	0.7	6
393	Electron and HolegFactors and Exchange Interaction from Studies of the Exciton Fine Structure inIn0.60Ga0.40AsQuantum Dots. Physical Review Letters, 1999, 82, 1748-1751.	2.9	378
394	Low-threshold high-quantum-efficiency laterally gain-coupled InGaAs/AlGaAs distributed feedback lasers. Applied Physics Letters, 1999, 74, 483-485.	1.5	82
395	Er doped nanocrystalline ZnO planar waveguide structures for 1.55 Î¼m amplifier applications. Applied Physics Letters, 1999, 75, 2005-2007.	1.5	83
396	Edge-emitting GaInAs-AlGaAs microlasers. IEEE Photonics Technology Letters, 1999, 11, 943-945.	1.3	48

#	Article	IF	Citations
397	InGaAs/AlGaAs quantum dot DFB lasers operating up to 213Â°C. Electronics Letters, 1999, 35, 2036.	0.5	20
398	Optical and structural properties of GaInAs/InP single quantum wells grown by solid-source MBE with a GaP decomposition source. Journal of Crystal Growth, 1998, 191, 607-612.	0.7	9
399	Exciton-photon interaction in low-dimensional semiconductor microcavities. Journal of Experimental and Theoretical Physics, 1998, 87, 723-730.	0.2	3
400	Hydride vapour phase epitaxy for nanostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1998, 51, 238-241.	1.7	6
401	Focused ion-beam implantation induced thermal quantum-well intermixing for monolithic optoelectronic device integration. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 595-605.	1.9	36
402	Zeeman splitting of excitons and biexcitons in singleIn0.60Ga0.40As/GaAsself-assembled quantum dots. Physical Review B, 1998, 58, R7508-R7511.	1.1	121
403	Weak and strong coupling of photons and excitons in photonic dots. Physical Review B, 1998, 57, 9950-9956.	1.1	112
404	High-temperature properties of GaInAs/AlGaAs lasers with improved carrier confinement by short-period superlattice quantum well barriers. Applied Physics Letters, 1998, 73, 2863-2865.	1.5	41
405	Focused ion beam implantation for opto- and microelectronic devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2562.	1.6	15
406	1.55 Î¼m single-mode lasers with combined gain coupling and lateral carrier confinement by focused ion-beam implantation. Applied Physics Letters, 1998, 73, 2703-2705.	1.5	7
407	Exciton-photon coupling in photonic wires. Physical Review B, 1998, 57, R6807-R6810.	1.1	33
408	Optical Modes in Photonic Molecules. Physical Review Letters, 1998, 81, 2582-2585.	2.9	359
409	Maskless selective growth of InGaAs/InP quantum wires on (100) GaAs. Applied Physics Letters, 1997, 70, 2828-2830.	1.5	8
410	Excitonic wave packets inIn0.135Ga0.865As/GaAs quantum wires. Physical Review B, 1997, 55, 9290-9293.	1.1	12
411	Laser emission from photonic dots. Applied Physics Letters, 1997, 71, 488-490.	1.5	31
412	Microcavity lasers: emission from a fully confined photon state. , 1997, , .		0
413	Enhancement of spontaneous emission rates by three-dimensional photon confinement in Bragg microcavities. Physical Review B, 1997, 56, R4367-R4370.	1.1	47
414	Size Dependence of Confined Optical Modes in Photonic Quantum Dots. Physical Review Letters, 1997, 78, 378-381.	2.9	128

#	Article	IF	Citations
415	Enhanced exciton-phonon scattering inInxGa1â^'xAs/GaAsquantum wires. Physical Review B, 1997, 56, 12096-12099.	1.1	16
416	Focused ion beam technology: A new approach for the fabrication of optoelectronic devices. , 1997, , .		1
417	Angle Resolved Photoluminescence Excitation Spectroscopy of Excitonâ€"Photon Modes in a Microcavity: K-Dependence and Relaxation. Physica Status Solidi A, 1997, 164, 81-84.	1.7	1
418	Reduced lateral straggling of implantation induced defects in III/V heterostructures by ion implantation along channeling directions. Applied Physics Letters, 1996, 68, 102-104.	1.5	1
419	Gain-coupled distributed feedback lasers in the blue-green spectral range by focused ion beam implantation. Journal of Crystal Growth, 1996, 159, 591-594.	0.7	2
420	First order gain and index coupled distributed feedback lasers in ZnSeâ€based structures with finely tunable emission wavelengths. Applied Physics Letters, 1996, 68, 599-601.	1.5	16
421	First order gainâ€coupled GaInAs/GaAs distributed feedback laser diodes patterned by focused ion beam implantation. Applied Physics Letters, 1996, 69, 1906-1908.	1.5	20
422	Gain-modulated second order distributed feedback gratings fabricated by maskless focused ion beam implantation in GaInAsP heterostructures. Microelectronic Engineering, 1995, 27, 343-346.	1.1	8
423	A closed UHV focused ion beam patterning and MBE regrowth technique. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 35, 208-213.	1.7	7
424	Implantation induced damage in. Nuclear Instruments & Methods in Physics Research B, 1995, 99, 594-597.	0.6	1
425	Dynamics of carrier-capture processes inGaxIn1â^'xAs/GaAs near-surface quantum wells. Physical Review B, 1995, 51, 4657-4660.	1.1	27
426	First-order gain-coupled (Ga,In)As/(Al,Ga)As distributed feedback lasers by focused ion beam implantation and in situ overgrowth. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2714.	1.6	6
427	GaInAs/GaAs quantum wire laser structures with strong gain coupling defined by reactive ion etching. Electronics Letters, 1995, 31, 457-458.	0.5	11
428	Gain-coupled distributed-feedback GaInAs-GaAs laser structures defined by maskless patterning with focused ion beams. IEEE Photonics Technology Letters, 1995, 7, 845-847.	1.3	6
429	Roomâ€temperature stimulated emission of optically pumped GaAs/AlAs quantum wires grown on (311)Aâ€oriented substrates. Applied Physics Letters, 1994, 64, 3443-3445.	1.5	5
430	Minimum feature sizes and ion beam profile for a focused ion beam system with post-objective lens retarding and acceleration mode. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 3518.	1.6	26
431	High resolution focussed ion beam implantation with post objective lens retarding and acceleration. Microelectronic Engineering, 1994, 23, 119-122.	1.1	6
432	Reactive ion etching of InAlAs with Ar/Cl2 mixtures for ridge waveguide lasers. Microelectronic Engineering, 1993, 21, 345-348.	1.1	4

#	Article	IF	Citations
433	Observation of a novel form of ordering in Al0.5In0.5As and (Ga,Al)0.5In0.5As. Journal of Crystal Growth, 1993, 131, 419-425.	0.7	5
434	Growth studies of (Al,Ga,In)As on InP by molecular beam epitaxy. Journal of Crystal Growth, 1993, 127, 755-758.	0.7	9
435	Influence of the cap layer thickness on the optical properties of near surface GaInAs/GaAs quantum wells. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 21, 198-200.	1.7	5
436	Transform-limited picosecond optical pulses from a mode-locked InGaAs/AlGaAs QW laser with integrated passive waveguide cavity and QW modulator. IEEE Photonics Technology Letters, 1993, 5, 896-899.	1.3	16
437	Optical properties ofGa0.8In0.2As/GaAs surface quantum wells. Physical Review B, 1993, 48, 14741-14744.	1.1	58
438	Excitonic transitions in GaInAs/GaAs surface quantum wells. European Physical Journal Special Topics, 1993, 03, C5-265-C5-268.	0.2	1
439	Gallium desorption during growth of (Al,Ga)As by molecular beam epitaxy. Applied Physics Letters, 1992, 61, 1222-1224.	1.5	21
440	Highâ€power singleâ€mode AlGaAs lasers with bentâ€waveguide nonabsorbing etched mirrors. Journal of Applied Physics, 1992, 72, 2131-2135.	1.1	16
441	50 mW CW-operated single-mode surface-emitting AlGaAs lasers with 45 degrees total reflection mirrors. IEEE Photonics Technology Letters, 1992, 4, 698-700.	1.3	18
442	Characterization of (In,Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simulations. Applied Surface Science, 1991, 50, 92-96.	3.1	9
443	MBE growth and post-growth annealing of GaAs-based resonant tunneling structures, viewed in relation to interface roughness. Journal of Crystal Growth, 1991, 111, 1100-1104.	0.7	5
444	Indium desorption during MBE growth of strained InGaAs layers. Journal of Crystal Growth, 1991, 111, 407-412.	0.7	42
445	Experimental evidence for the transition from two- to three-dimensional behavior of excitons in quantum-well structures. Physical Review B, 1991, 43, 4933-4938.	1.1	40
446	Band offset in elastically strained InGaAs/GaAs multiple quantum wells determined by optical absorption and electronic Raman scattering. Applied Physics Letters, 1990, 56, 536-538.	1.5	89
447	Confinement of light hole valenceâ€band states in pseudomorphic InGaAs/Ga(Al)As quantum wells. Applied Physics Letters, 1990, 57, 957-959.	1.5	23
448	Response to â€˜â€˜Comment on â€˜Investigation of the critical layer thickness in elastically strained InGaAs/GaAlAs quantum wells by photoluminescence and transmission electron miscroscopyâ€™â€‰â€™â€™ [Appl. Phys. Lett.55, 2147 (1989)]. Applied Physics Letters, 1989, 55, 2147-2148.	1.5	2
449	Investigation of the critical layer thickness in elastically strained InGaAs/GaAlAs quantum wells by photoluminescence and transmission electron microscopy. Applied Physics Letters, 1989, 54, 48-50.	1.5	51
450	Tailored InP-based quantum dash structures for ultra-wide gain bandwidth applications. , 0, , .		1

#	Article	IF	Citations
451	First order gratings for gain coupled GaInAsP DFB-lasers made by maskless focused ion beam patterning. , 0, , .		0
452	Gain-coupled distributed feedback lasers made by focused ion beam implantation: process parameters and device properties. , 0, , .		1
453	A new approach for the fabrication of gain-coupled DFB laser diodes using focused ion beams. , 0, , .		0
454	Focused ion beam implantation for gain coupled 1.55 Î¼m DFB-laser diodes with improved device characteristics. , 0, , .		0
455	High performance laterally gain coupled InGaAs/AlGaAs DFB lasers. , 0, , .		2
456	High performance GaInAs/AlGaAs quantum-dot light emitting diodes and lasers. , 0, , .		0
457	Edge-emitting microlasers with a single quantum dot active layer. , 0, , .		0
458	Monolithic integration of laterally complex coupled DFB lasers with passive waveguides by positive wavelength detuning. , 0, , .		0
459	Integration of 2D photonic crystals in InP laserdiodes. , 0, , .		0
460	1.3 Î¼m quantum-dot lasers with improved high temperature properties. , 0, , .		0
461	Quantum dot lasers for high power and telecommunication applications. , 0, , .		1
462	Quantum-dot microlasers as high-speed light sources for monolithic integration. , 0, , .		1
463	Self-assembled quantum-dash lasers on the InP system. , 0, , .		4
464	Two- and three-sectional laterally coupled DBR laser fabricated by focused ion beam lithography. , 0, , .		0
465	InAs/InGaAlAs/InP quantum dash lasers for telecommunication applications. , 0, , .		1
466	22 GHz direct-modulated weakly coupled DBR-laser fabricated by focused ion beam lithography. , 0, , .		0
467	Quantum dot semiconductor lasers. , 0, , .		0
468	Experimental investigations into the thermal properties of 1.5-1.8-Î¼m InAs/InP quantum dash lasers. , 0, , .		0

#	Article	IF	Citations
469	Ultra-short GaAs/AlGaAs quantum-cascade micro-lasers based on monolithically integrated semiconductor-air Bragg-mirrors. , 0, , .		0
470	Modulation speed enhancement by coupling to higher order resonances: a road towards 40 GHz bandwidth lasers on InP. , 0, , .		16
471	InP-based quantum dash lasers for broadband optical amplification and gas sensing applications. , 0, , .		2
472	Controllable Switching between Single Modes in Two-Segment Distributed Feedback Quantum-Cascade Lasers. , 0, , .		0
473	Experimental and Theoretical Investigations on Spectral Gain Bandwidth of Broadband (<300 nm) InP based Quantum Dash Material. , 0, , .		0
474	Ultrashort quantum dot microlasers. , 0, , .		0